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RESEARCH ON ELECTRON BOMBARDMENT INDUCED CONDUCTIVITY TARGETS IN CAMERA TUBES

TECHNICAL REPORT No. ASD-TR-61-657

APRIL 1962

ELECTRONIC TECHNOLOGY LABORATORY
AERONAUTICAL SYSTEMS DIVISION
AIR FORCE SYSTEMS COMMAND
WRIGHT-PATTERSON AIR FORCE BASE, OHIO

Project No. 4156, Task No. 415605

(Prepared under Contract No. AF 33(616)-6496 by Westinghouse Research Lab., Pittsburgh, Pa. Authors: J. Lempert and G. Klotzbaugh)
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FOREWORD

This report was prepared by Westinghouse Research Laboratories, Pittsburgh, Pennsylvania, on Air Force Contract AF 33(616)-6496, under Task No. 415605 of Project No. 4156, "Electronic Tube Technology". The work was administered under the direction of Electronic Technology Laboratory, Aeronautical Systems Division. Mr. Melvin R. St. John was Project Engineer for the Laboratory.

The studies presented began in May 1959 and this report describes the research performed during the period from October 1960 through October 1961.

The experimental tubes built on this program were fabricated under the supervision of Mr. A. Crans and Mr. D. Doughty, and evaluated by Dr. G. Klotzbaugh. Mr. J. Lempert was responsible for the target program and served as principal investigator.
ABSTRACT

An analysis of scan parameters as they affect the performance of electron bombardment induced conductivity (EBIC) targets is presented. The conclusion is reached that the secondary emission characteristic of the target surface is an extremely important parameter in camera tubes of the photoconductivity and EBIC types. Evidence that the electron absorptivity of the target for low voltage electrons is affected by the degree of induced excitation is presented. Results of an investigation of different EBIC target materials are reviewed. The fabrication of experimental EBIC tubes having electrostatic and magnetic focused image sections is described. Test results to date are discussed.

PUBLICATION REVIEW

The publication of this report does not constitute approval by the Air Force of the findings or conclusions contained herein. It is published only for the exchange and stimulation of ideas.

FOR THE COMMANDER:

AMOS H. DICKE
Chief, Thermionics Branch
Electronic Technology Laboratory

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1) Introduction

This report summarizes work performed over the past year in the study of thin high gain films of the electron-bombardment-induced conductivity (EBIC) type. The principal emphasis in this work has been on a search for improved EBIC materials, and on a study directed toward obtaining a better understanding of target parameters affecting the quality of scan.

The general objective of the target investigation has been the development of materials having higher gains than were available heretofore, having short decay times as well as the ability to withstand the type of environment associated with camera tube exhaust. High target gain (Ref. 1) is important because it leads directly to improvement in threshold sensitivity for camera tubes using both vidicon and return beam multiplier scan.

The improvement in the ability of a given target to withstand exhaust environment refers to its capability for withstanding exhaust temperatures as well as exposure to cesium and other metallic vapors, associated with the sensitization of photosurfaces. Inability of available target materials to withstand temperatures in excess of 1500°C has made it necessary to cool the target during tube bake-out. As a result parts of the tube in the immediate vicinity of the target were not outgassed as well as more remote regions of the tube. In addition there was a tendency for cesium vapors released during sensitization to condense on the cooler parts of the tube. The condensation problem is expected to be a serious one for tubes employing multialkali photosurfaces.

A technique for injecting the target into the tube after the sensitization of the tube has been completed, which is discussed in more detail in the next section, has promise of circumventing the problems associated with the exhaust environment of the tubes. This technique, once perfected, may eliminate the necessity for development of a target which is resistant to the environment present within the interior of a given tube during exhaust.

As noted in a later section, the mechanism for excitation and amplification of photoconductivity (PC) and EBIC type camera tube targets under certain conditions may be somewhat different from that usually stipulated. The mechanism for imaging for vidicon PC type tubes is usually considered to be the following:

The scan surface of the target, in the absence of excitation, is brought by action of the scan beam to a minimum equilibrium potential, \( V_0 \), which is near to cathode potential. The target surface after being scanned may be considered to be essentially biased off from the gun, and negligible beam landing occurs. Because of the potential gradient across the target resulting from application of target potential \( V_m \), "dark" current leaks through the target to the backplate. As a result, the potential of the scan surface of the target rises slightly by an amount \( \Delta V \). Hopefully this increase in potential is uniform over the target raster area and information on target non-uniformities is not conveyed to the monitor as a background spurious signal when the scan beam restores the target to its minimum potential \( V_0 \).

Manuscript released by authors October 1961 for publication as an ASD Technical Report.

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Excitation, whether optical or by high velocity electrons, now increases the number of charge carriers within the target volume, thereby decreasing the resistance of excited areas in proportion to the degree of excitation. As a result the scan surface leaks to a more positive signal potential \((\Delta V)_s\), relative to neighboring dark areas, which as indicated previously reach a maximum potential \((\Delta V)_D\) above the minimum equilibrium potential of the target, \((V_0)_D\). The action of the scan beam now brings all areas of the target back to the equilibrium potential \((V_0)_D\), the effective signal, \(I_T\), from the excited areas being:

\[
I_T = \frac{\Delta Q}{\Delta t} = \frac{c \left[ (\Delta V)_s - (\Delta V)_D \right]}{\Delta t}
\]

where \(\Delta t\) is the time a given raster element having an integrated signal charge \(\Delta Q\) is scanned, and \(c\) is its capacitance. Beam landing occurs only until signal areas are brought to their minimum potential, at which time the target cuts off. The landing current required to charge the target scan surface to \((V_0)_D\) constitutes the video signal. The video signal thus is derived directly from the ability of the beam to land in proportion to the signal voltage strength of a given area. The signal thus generated is capacitively coupled to the backplate where it is fed directly to the preamplifier stage. The mechanism for imaging above described will be referred to henceforth in this report as "signal discharge imaging", since the implication of complete or almost complete signal discharge is present in this imaging mechanism.

During the course of the study of target scan parameters it became evident that signal discharge imaging as described above does not necessarily fully depict the sequence of events responsible for producing video signals for all target materials under all conditions of operation. At least two other effects appear to be involved in the mechanism for producing video signals. All three of the modes of operation are probably usually involved in varying degrees, depending on the condition of the target and the target materials.

The first of the two alternative modes for scan type imaging with PC and EBIC surfaces, which will be described in detail in a later section, will be referred to as target voltage modulation imaging, the other as charge carrier beam modulation imaging. Information on the former mode for imaging derives directly from measurements and analyses which indicate that the scan beam does not necessarily bring signal areas to the same minimum potential \((V_0)_S\) that the dark areas reach as the result of the scan operation. Thus the signal areas are not necessarily discharged or nearly discharged as assumed in "signal discharge imaging".

The target surface does not bias off from the beam and landing occurs through the entire scan interval. The difference in signal response between a dark area and a signal area relates to the average electron absorptivity of the target surface to scan beam electrons as it undergoes a potential shift during the interval beam landing occurs. If the secondary emission ratio which applies to the surface of a given signal area on the target at an
average potential $\overline{V}_s$ is $\overline{D}$, then the electron absorptivity of this area of the target to scanning beam electrons may be defined as $(1-\overline{D})$, where $\overline{D}$ is a function of $\overline{V}_s$. If $I_B$ is the scan beam current impinging on the target, then the signal current $I_T$ is determined by the magnitude of $I_B(1-\overline{D})$. Using this terminology, the magnitude of the dark current will be given by $I_B(1-\overline{D})$, where $(1-\overline{D})$ is the electron absorptivity which applies to the average potential of the surface in dark areas of the target. The slope of the $\overline{D}$ versus $\overline{V}$ curve turns out to be a significant factor in determining contrast and shades of grey when this type of imaging takes place. When target voltage beam modulation occurs, an increase in $I_B$ or a decrease in $\overline{D}$ or both may decrease $\overline{V}_o$, the potential of a signal area after scan, until it is substantially equal in magnitude to $(\overline{V}_o)_{D}$, the dark current minimum equilibrium potential. Signal discharge imaging will then occur, since the condition for full discharge of a signal area is then met. It is evident that the signal discharge mode of imaging is a special case of the target voltage modulation mode.

The term charge carrier beam modulation imaging derives directly from measurements described in a later section which indicate that the electron absorptivity of the target for slow electrons may be significantly affected by the excitation conditions which occur in a given area of the target. It is likely that the number of excited charge carriers and the distribution of trapping and recombination states, affect the retention capabilities of the targets as far as the low velocity electrons of the scan beam are concerned. In this mode of imaging the target absorptivity to scan beam electrons is affected both by the average potential of the target surface and by the conditions of carrier excitation. There is also evidence to indicate that the scan beam electrons which are absorbed or retained by the target can affect the conductivity of certain targets. It is evident that further study of the various mechanisms associated with charge carrier scan beam modulation is required.

It is believed that the work on scan variables, described in a later section, will benefit the program from the standpoint of assisting in the understanding of target parameters which are beneficial for imaging, as well as in the determination of whether parameters useful for vidicon scan are the optimum parameters for scan using a return beam multiplier. In addition this work should materially contribute to the development of techniques for evaluating the performance of a given target, which is a prime necessity to the target research program.

2) Army Signal Corps Program

The work performed for the Signal Corps on Contract DA-36-039 SC-87397 during the past period has been largely concerned with the study of factors affecting the performance of an EBIC camera tube having a multiplier in the return beam. This work has encompassed (a) A study of factors limiting the resolution of the scan section, (b) A study of scan parameters as they affect EBIC target performance. The aspects of this work which are pertinent to the evaluation of targets has a common basis with the Air Force Program and is
summarized in Section 3 of this report. (c) Work on magnetically focused high
voltage image sections. (d) A detailed study of the properties of As$_2$S$_3$ and
As$_2$Se$_3$ type EBIC targets. (e) The work referred to previously on developing
a method for injecting the EBIC target into the EBIC camera tube. This technique
involves storing the target in a protected location in a side tubulation until
the tube is outgassed, the photosurface is sensitized, and the tube is ready
to be tipped off the pumps. A major problem has concerned the developing of
techniques to seal off the connecting tubulation. This technique has been
reasonably successful and has been applied to experimental tubes fabricated
on the Air Force program which will be described later in this report.

3) Investigation of Scan Parameters as They Affect Target Performance

   a. Simplified Theory of Target Scan

When a camera tube having a photoconductive or an EBIC type target
is employed for continuous imaging of a fixed scene, an equilibrium condition
is reached in which the amount of charge deposited by the beam is equal to the
amount of signal charge which leaks from the scan surface to the backplate of
the target.

This equilibrium may be described by the following equation:

\[ I_T = \frac{V_T - \bar{V}_s}{R} = I_B (1-\delta) \]  \hspace{1cm} (2)

where \( I_T \) is the average target signal current, \( V_T \) is the target backplate
voltage, \( \bar{V}_s \) is the average DC potential reached by the target surface. \( R \) is
the total effective resistance of the excited target in ohms; \( I_B \) is the
magnitude of the beam current landing on the target in amperes, and \( \delta \) is the
value of the secondary emission ratio which is applicable to the average sur-
face potential of the target \( V_s \). In the following the assumption is made that
\( \delta \) is a function of \( V_s \) only and not of other parameters such as the input
excitation.

An equation similar to (2) applies to the dark current which is
drawn through the target in the absence of excitation:

\[ (I_T)_D = \frac{V_T - V_{\text{D}}}{R_D} = I_B (1-\delta) \]  \hspace{1cm} (3)

where \((I_T)_D\) and \(R_D\) are the target current and resistance associated with the
unexcited target under scan conditions.

* This section summarizes work performed under joint sponsorship of Signal
Corps on Contract DA-36-039 SC-87397 and WADD on Contract AF 33(616)-6496.
The contributions to beam velocity produced by the Maxwellian distribution of electrons leaving the hot cathode, and contact potential effects have been neglected in this analysis. The effect of these variables on target performance has been discussed in Ref. (1). This reference also includes a more general treatment of target scan parameters than is presented here.

The electric field gradients across PC and EBIC targets (which are of the order of 50,000 to 500,000 volts/cm) exceed those in the case of common semiconductors such as Ge and Si for which Ohm's law normally applies (1,000-10,000 volts/cm). For materials having low band gaps, when the velocity imparted to the electrons in one mean free path becomes comparable to the thermal velocities of the electrons in the solid, substantial departures from Ohm's law have been observed (Ref. 2, 3). The mobility of the charge carriers in these materials exhibits an $E^{1/2}$ power relationship after a critical gradient is exceeded. In order for Ohm's law to hold, the number of charge carriers and the mobility of these carriers should be independent of the field gradient. Apparently the conditions for Ohm's law to apply are approximately filled at high field gradients in certain photoconductors which have relatively large values of band gaps. Amorphous selenium has been observed to meet the conditions for ohmic behavior when exposed to low intensity illumination (Ref. 4). At higher excitation levels, the target current varies according to the square of the voltage across the target, a relationship consistent with the passage of space-charge-limited currents.

The photo-excited currents in $Sb_2S_3$ photoconductive materials have been found to vary with the first power of voltage across the target (Ref. 5), which is indicative of ohmic behavior. At fixed values of EBIC excitation, the variation of signal currents through $As_2S_3$ targets (Ref. 1) with the voltage impressed across the target can also be approximated by a first power relationship. Similarly, many of the other experimental materials investigated show the same approximate relationship. Ioffe (Ref. 6) has observed that the photoconductive conductivity is independent of the field gradient for pure materials. However, the experimental work apparently did not exceed gradients of 45,000 volts/cm.

In view of the above, the assumption is made in the following analysis that the behavior of PC and EBIC materials under excitation follow Ohm's law. In the case of non-ohmic behavior it is necessary to perform an averaging operation on eqs. (2) and (3) in which the variation of the target resistance with field in considered.

As a result of the leakage type signal currents, which are characteristic of PC or EBIC type targets, the instantaneous value of target surface potential under uniform continuous excitation will rise from a minimum value $V_0$ to a maximum value of surface potential $V_m$ during frame time. Under equilibrium conditions the deposition of electrons from the
gun during the scan interval will reduce the surface potential back to $V_0$ immediately upon conclusion of the scan action on any given target element. This equilibrium condition may be represented mathematically by the following equation:

$$\Delta Q_W = \Delta Q_R = \Delta V C = (V_m - V_o)C = I_T T$$  \hspace{1cm} (4)$$

where $(\Delta Q)_W$ and $(\Delta Q)_R$ represent the electrical charge transported during the writing and reading operations, $\Delta V = (V_m - V_o)$ is the change in potential produced as a result of the writing and reading actions, $T$ is frame time, and $C$ is the capacity of the target raster.

Using standard condenser discharge equations, the instantaneous potential of the target surface during the writing interval may be expressed by the following equation:

$$V_s = V_T - (V_T - V_o)e^{-t/RC}$$  \hspace{1cm} (5)$$

where $V_s = V_o$ at $t = 0$. Since the target surface reaches $V_m$ potential at the completion of the writing interval $T$,

$$V_m = V_T - (V_T - V_o)e^{-T/RC}$$  \hspace{1cm} (6)$$

and

$$\Delta V = V_m - V_o = (V_T - V_o)(1 - e^{-T/RC})$$  \hspace{1cm} (7)$$

$$V_o = V_T - \frac{\Delta V}{(1 - e^{-T/RC})}$$  \hspace{1cm} (8)$$

As beam current $I_B$ is increased, $V_o$ will decrease until it approaches a minimum equilibrium value which is very close in magnitude to $(V_o)_D$, the potential of dark areas of the target immediately after being scanned. $(V_o)_D$ and hence $V_o$ for high $I_B$ is assumed to coincide with the zero reference of potential for target backplate voltage. Thus for the condition of high beam eq. (8) becomes:
Expressing eq. (9) in terms of $R$, and expanding in a series,

$$R = -\frac{T}{C} \ln(1 - \frac{\Delta V}{V_T}) = \frac{T}{C} \left(\frac{\Delta V}{V_T} + \frac{1}{2} \left(\frac{\Delta V}{V_T}\right)^2 + ...\right)$$

Neglecting the higher power terms, and substituting for $V$ using eq. (4), we obtain for the case of high beam:

$$R = \frac{TV_T}{C\Delta V}$$

which is also the expression obtained by use of eq. (2) assuming $V_s$ is zero due to high beam.

In order to determine the corresponding equations for action of the scanning beam, it is necessary to have a knowledge of the variation of the secondary emission ratio as a function of $V$. The typical variation of secondary emission ratio with surface potential can be approximated by an equation of the following form:

$$\delta = 1 - aV_s + bV_s^2$$

Consider a raster element having capacity $C_R$. If it is exposed to the beam for time $t$, the element will decrease in potential from $V_m$ to $V_s$ according to the equation:

$$C_R (V_m - V_s) = \int_0^t I_B (1 - \delta) dt.$$ 

Differentiating:

$$\delta = 1 - aV_s + bV_s^2.$$
By integrating for the time \( \tau_o \) required to scan a raster element, the following equation is obtained:

\[
\frac{dV_s}{dt} = I_B (1 - \delta) = I_B (aV_S - bV_s^2). \tag{14}
\]

\[
-C_R \frac{dV_s}{dt} = I_B (1 - \delta) = I_B (aV_S - bV_s^2). \tag{14}
\]

For the low voltage portions of the \( \delta \) vs \( V_s \) curves, the last term in eq. (12) can be neglected, and eq. (16) takes the form:

\[
V_o = V_m e^{\frac{-aI_B T}{C}}. \tag{17}
\]

By using the equality

\[
\Delta V = (V_m - V_o) = \frac{I_T T}{C}, \tag{18}
\]

eq. (16) can be solved for \( V_o \) giving:

\[
V_o = \frac{a}{2b} - \frac{\Delta V}{2} + \frac{1}{2} \sqrt{(\frac{a}{b})^2 - 2(\frac{a}{b}) \Delta V + (\Delta V)^2} - \frac{a I_B T}{b I_B}. \tag{19}
\]
In solving eq. (16) for $V_0$, the exponential is expanded into a power series. Little loss in accuracy is obtained when the first two terms of the series are used for values of $(aI_B/C)$ less than 0.1, which are usually the case.

The average surface potential $\bar{V}_s$ can be obtained directly from eqs. (2) and (12) as follows:

$$I_T = I_B (1 - \delta) = I_B (a\bar{V}_s - b\bar{V}_s^2).$$

Solving the above quadratic for $\bar{V}_s$ gives

$$\bar{V}_s = \frac{a}{2b} \pm \frac{1}{2} \sqrt{\left(\frac{a}{b}\right)^2 - \frac{4}{b} \frac{I_T}{I_B}}$$

Substituting in eq. (12) for $\delta = 1$, it is evident that the first crossover potential corresponds to $a/b$ volts. By differentiating this equation, it is evident that the minimum potential on the curve of $\delta$ vs. $\bar{V}_s$ which will be defined as $(\bar{V}_s)_0$, is equal to $a/2b$ volts.

Equations (8) and (19), which are derived from the scan and writing parameters respectively, together with eq. (18), define the general performance of a scan system under equilibrium between the scan and writing actions.

While $\bar{V}_s$ can be determined as a function of $I_T$ from simple scan parameters, in order to determine $V$, it is necessary also to have a knowledge of factors affecting wave form, such as frame time $T$ and the capacitance of the target. Since $\Delta V$ in most EBIC applications is substantially under a volt, a fairly close approximation to the potential situation on the target can be obtained by assuming $V_0 = \bar{V}_s - \Delta V/2$, and $V_m = \bar{V}_s + \Delta V/2$.

A better understanding of the target parameters can be obtained by utilizing a specific functional relationship between $\delta$ and $\bar{V}_s$. The typical $\delta$ function shown at the left of Fig. 1 is based on the following equation:

$$\delta = 1 - 1.7 \times 10^{-2} \bar{V}_s + 2.8 \times 10^{-4} \bar{V}_s^2$$

The variation of $I_T$ and $\bar{V}_s$ as a function of $V_m$ shown in Fig. 1 has been determined using eq. 2, assuming that eq. (22) applies to the surface, and that the target resistance is $10^3$ ohms. It is evident that the resistance of the target is only one of the variables which determines the signal current for a given value of backplate voltage. The maxima on the signal
Fig. 1 -- EBIC target scan parameters assuming target resistance $R = 10^9$ ohms and
$$
\delta = 1 - 1.7 \times 10^{-2} V_s + 2.8 \times 10^{-4} V_s^2
$$
for indicated values of $I_B$. 

$-10-$
versus target backplate potential curves always correspond to the value of target surface potential, \( (V_s)_0 \), for which the potential difference across the target, \( (V_T - V_s) \), is a maximum. The maximum possible signal current is thus given by the product of \( I_B \) by the \( (1-\delta) \) value which corresponds to \( (V_s)_0 \). It is interesting to note that the maximum signal is not determined by the target resistance or backplate potential.

The curves of Fig. 2 have been derived for a fixed beam current of \( 3 \times 10^{-7} \) amperes. Different values of target resistance between \( 10^9 \) and \( 2 \times 10^9 \) are assumed. The constancy of the maximum value of \( (I_T) \) observed in this figure despite the variation of \( R \) graphically illustrates that the specific value of the maximum is dependent only on \( I_B (1-\delta) \) max. Referring to the upper curve of Fig. 2, it is evident that the \( I_T \) maxima all occur at \( V_s = 30 \) volts, as would be expected.

The \( I_T \) vs \( V_m \) curves of Fig. 1 will be observed to approach a limiting curve defined by eq. (11) as \( I_B \) is increased. Signal discharge imaging as defined previously would be expected to take place as \( I_T \) approaches the limiting curve, and \( V_s \) approaches zero potential.

From Fig. 2 for a beam current of \( 3 \times 10^{-7} \) amperes and a target backplate voltage of 40 volts, it is evident that signal currents in excess of \( 1 \times 10^{-8} \) amperes involve appreciable values of \( V_s \). Table I below lists the \( I_T \) and \( V_s \) values associated with the different values of target resistance shown in Fig. 2. The column at the right-hand side of this table gives \( \Delta V \) on the assumption that the raster is that of a standard vidicon having an area of 3/8" x 1/2". A 2\( \mu \) target thickness is assumed and a dielectric constant of 6.25.

**TABLE I**

<table>
<thead>
<tr>
<th>R (ohms)</th>
<th>( I_T ) (amperes)</th>
<th>( V_s ) (volts)</th>
<th>( \Delta V ) (volts)</th>
</tr>
</thead>
<tbody>
<tr>
<td>( 2 \times 10^9 )</td>
<td>( 1.8 \times 10^{-8} )</td>
<td>3.0</td>
<td>.18</td>
</tr>
<tr>
<td>( 10^9 )</td>
<td>( 3.3 \times 10^{-8} )</td>
<td>7</td>
<td>.33</td>
</tr>
<tr>
<td>( 6 \times 10^8 )</td>
<td>( 4.8 \times 10^{-8} )</td>
<td>11</td>
<td>.48</td>
</tr>
<tr>
<td>( 3 \times 10^8 )</td>
<td>( 6.6 \times 10^{-8} )</td>
<td>20</td>
<td>.66</td>
</tr>
<tr>
<td>( 10^8 )</td>
<td>( 7.7 \times 10^{-8} )</td>
<td>32</td>
<td>.77</td>
</tr>
</tbody>
</table>

From this table it is evident that a target having secondary emission characteristics defined by eq. (22) will require beam currents substantially in excess of \( 3 \times 10^{-7} \) amperes if signal discharge imaging is to be...
Fig. 2--EBIC target scan parameters for \( \bar{\sigma} = 1 \cdot 1.7 \times 10^{-2} \bar{V}_s + 2.8 \times 10^{-4} \bar{V}_s^2 \) the indicated values of target resistance in ohms and \( I_B = 3 \times 10^{-7} \) A
approached. For the $3 \times 10^{-7}$ amperes beam current used in Table I, target voltage modulation imaging, as defined previously, will occur. In this mode of imaging the secondary emission characteristic of the surface play an important role in determining the signal and contrast levels attained. In signal discharge imaging on the other hand, the secondary emission characteristics of the target determine the amount of beam required to attain this form of imaging, but play no further role in determining the imaging characteristics of the target.

It is interesting to note that the ratio of the highest to the lowest resistance in Table I is 5, and that the corresponding ratio for signal current is only 4.53. This is equivalent to .94 power variation of signal current with input excitation. The departure from first power variation is related only to the secondary emission characteristic of the target surface, and does not involve solid state parameters.

A graph of the type shown in Fig. 3 is useful for visualizing the effect of the various parameters involved in the scanning of PC and EBIC type targets. The beam landing and remaining on target, $I_B(1-\delta)$, is plotted for various beam currents as a function of $V_s$, where $\delta$ is assumed to be defined by eq. (22). The target leakage current, obtained from the equation $(V_T-V_s)/R$, is also plotted on the same graph as a function of $V_s$. The load lines shown in the diagram correspond to all the possible average leakage currents through the target for target resistances of $2 \times 10^9$ and $10^{10}$ ohms and a backplate potential of 50 volts. These load lines are fixed by the knowledge that the signal current is zero when $V_s = V_T$, and equal to $V_T/R$ when $V_s = 0$.

The intersection of a given load line with an $I_B(1-\delta)$ curve represents a possible point of equilibrium, since the leakage current through the target is equal to the current deposited by the beam at this point in the diagram. When the target backplate potential is greater than the first crossover potential of the target, a given load line will make two intersections with a given beam landing line, one above $(V_s)_0$, the other below it. Intersections or operating points which occur below $(V_s)_0$ meet the criteria for stable equilibrium situations since any departure of $V_s$ from the values corresponding to the intersection points will produce a flow of charge which will restore $V_s$ to its equilibrium value. For example, if $V_s$ fluctuates for any reason below the equilibrium value corresponding to a given operating point, it is evident from Fig. 3 that the target leakage current will increase, and the beam landing current will decrease. Both of these changes are in a direction which makes the target more positive and restore the signal potential. Similarly for any fluctuation of surface potential which makes $V_s$ more positive than the potential corresponding to the intersection of the two curves, the landing current increases and the target leakage decreases, both effects again working toward shifting surface potentials back to equilibrium values.

Quite a different situation occurs for operating points above $(V_s)_0$. A fluctuation in $V_s$ which is more negative than the expected operating potential, will increase both the beam landing and the target leakage currents. From Fig. 3 it is evident that the beam landing will increase more rapidly than the target.
Fig. 3 -- As function of $\overline{V}_S$: Target leakage currents for different values of target resistance; also beam landing signal $I_B$ (1-6) for different values of $I_B$. 

-14-
leakage currents. Thus the target surface potential would shift progressively further away from the intersection value of \( V_s \) toward the stable operating point below \((V_s)_0\). Similarly, for fluctuations of \( V_s \) above the intersection value, the beam landing current will decrease more rapidly than the target leakage current, and the target surface would be expected to shift in the more positive direction away from the intersection potential and toward the first crossover point. Thus intersections of the curves of Fig. 3 which occur below \((V_s)_0\) may be expected to correspond to stable operating points, and those above \((V_s)_0\) to unstable operating points.

Referring to Fig. 1, for \( V_T = 90 \) volts, the points on the curves marked (1) correspond to stable and those marked (2) to unstable operating points.

The changes in \( I_T \) and \( V_s \) respectively as a function of \( I_B \) for a target backplate potential of 50 volts and different values of target resistance are shown in Figs. 4 and 5, again assuming that the secondary emission ratio of the surface is defined by eq. (22). The signal current curves saturate at high values of \( I_B \) as would be expected from Fig. 3. The plateau portions of the \( I_T \) vs \( I_B \) curves correspond to low values of \( V_s \). Any significant drop in \( I_T \) as \( I_B \) is decreased is, however, an indication of a substantial rate of rise in the value of \( V_s \).

Considerable information on a given target material can be obtained by making measurements corresponding to the plots of Fig. 4. The electron absorptivity of the target surface, \((1-\delta)\), for any given operating point is obtainable directly from the ratio \( I_T/I_B \). To obtain the corresponding values of \( V_s \), it is necessary only to solve eq. (11) for \( R \) using the saturated values of \( I_T \), and to substitute the value so obtained in the equation \( V_s = V_T - I_T R \) to obtain \( V_s \).

When the positive excursion of \( V_s \) is restricted by use of sufficient high values of \( I_B \), the low voltage portion of the \( \delta \) vs \( V_s \) curve can be approximated by an equation of the form:

\[
\delta = 1 - aV_s .
\]  

Using eq. (2) and eq. (23) the following expressions for \( V_s \) and \( I_T \) can be obtained:

\[
V_s = \frac{V_T}{(1 + aI_B R)} = \frac{I_T}{aI_B} \quad (24)
\]

\[
I_T = \frac{V_T}{R} \left( \frac{aI_B R}{(1+aI_B R)} \right) \quad (25)
\]

When \( aI_B R \) is large, as in the case of high beam, or high target resistance, or high value of "a", eq. (25) transforms into eq. (11). If we arbitrarily define signal discharge imaging as occurring when \( V_s \) is less than 1 volt, then
Fig. 4—Target signal current as function of beam current for various values of target resistance.
Assumes $V_T = 50$ volts and $\bar{\delta} = 1 - 1.7 \times 10^{-2} \bar{v}_s + 2.8 \times 10^{-4} \bar{v}_s^2$.
Fig. 5--Target surface potentials as function of beam current for parameters of Fig. 7.
from eq. (24) this condition is met when:

$$a I_B R \geq (V_T - 1)$$

(26)

The visual effect of varying $V_S$ by changing $I_B$ at a given constant excitation can be observed on the monitor of the camera tube. As $I_B$ is reduced from a relatively high value, little effect is observed initially corresponding to the saturation region, where little change in $I_T$ occurs as $I_B$ is initially decreased. A critical beam current is then reached below which the whites in the image are observed to diminish in brightness. Contrast then goes down markedly.

With some target materials it is possible to observe a definite gradation in the white areas at low values of $I_B$, which it is believed is attributable to beam bending. The image consists of black and white areas of reduced contrast due to the low beam. However, the white areas adjacent to the blacks are whiter than white areas which are more remote from the blacks. It is believed that the darker parts of the white areas have $V_S$ values which are greater than $(V_S)_0$. The whiter areas in the white images have had greater beam landing due to bending the beam directed at the blacks. Thus these areas have a lower $V_S$ value than the white areas which are remote from the blacks, and thus have greater values of $(1-\phi)$ and in consequence greater signal. Further diminishing of beam will cause the whiter areas of the white to blend into the blacks, and full image reversal is now experienced. The failure of the beam to land on the black areas due to beam bending has contributed substantially in the building up of the $V_S$ value of the black regions of the image.

The rate of increase of $V_S$ and decrease in $I_T$ with decreasing $I_B$ can also be assessed using Fig. 3. It is evident as $I_B$ is decreased not only does $I_T$ decrease but signal contrast, as given by $$[(I_T)^2 - (I_T)'(I_T)']/[(I_T)^2]$$ also decreases, where $(I_T)$ and $(I_T)'$, represent the signals associated with load lines corresponding to $R_2$ and $R_1$ ohms target resistance respectively. Depending on the resistance of the load lines selected, image contrast not only reduces with decreasing $I_B$ but also can reverse in polarity, i.e., a grey area at low $I_B$ values can furnish a higher signal output than the signal highlight area. If reversal occurs at very low $I_B$ values, it is also evident that as $I_B$ is reduced a range of signal levels will occur wherein the white area is equal to and hence indistinguishable from the image corresponding to the grey area.

By inspection of Fig. 3 it is apparent that it is desirable in the interest of large signals to operate at the highest possible target backplate voltage. Ordinarily, $V_T$ is limited by target non-uniformities, and by the possibility of parts of the target going over first crossover potential. It is also evident that it is desirable to utilize the highest beam possible. However, in the case of a tube with a return beam multiplier, as noted in Ref. (1), beam noise increases as $I_B^{1/2}$. Also, the scanning beam spot size tends to increase as beam level is increased. For these reasons, depending on the parameters of the target and the
input signal level used, an optimum value for setting of beam current will exist. In tube operation this is normally determined by adjusting beam current to produce optimum image quality at a given signal input level from the scene.

b. Experimental Investigation of Target Scan Parameters

In the previous section, a simplified theory of operation of EBIC and PC type targets was developed. In the derivation the secondary emission ratio of the target surface was assumed to be a function only of $V_s$ and not, for example, of the target excitation level. Characteristic curves were plotted assuming a specific relationship between $\delta$ and $V_s$ which was considered to be typical of an insulating material. It is evident that the general mechanism for imaging developed should in general be independent of the particular functional variation of $\delta$ with respect to $V_s$.

The simple theory assumed that the targets exhibit ohmic behavior, and that target resistance is a function only of the input excitation and not dependent, for example, on the voltage impressed across it, nor the magnitude of the beam current going to it. The accuracy of the determination of $V_s$ depends on the extent these assumptions hold. As indicated later in this section, it is believed that the assumption of ohmic response is a reasonable approximation for the field gradients which occur across the target on the measurements described here.

The method outlined in the previous section for determining target resistance and electron absorptivity of the target surface is employed in the present section to determine scan parameters of specific target materials, and to check the validity of the assumptions previously made.

The accuracy of the determination of $1-\delta = I_T/I_B$ in these measurements is largely a function of how accurately $I_B$ can be determined and the amount of drift experienced during a given set of readings. After comparative tests of different methods of determining $I_B$, the method finally used involved the measurement of the current to the focus electrode of the vidicon scan gun with the magnetic focus field off, and then making allowances for the anticipated electron transmission of the mesh structure at the extremity of the focus electrode.

An attempt was initially made to take $(1-\delta)$ characteristics of $\text{As}_2\text{S}_2$ and $\text{As}_2\text{S}_3$ targets using target dark current as the "signal" current. The attempt was abandoned when it was found that the dark current was so low for these materials it could not be determined in the demountable position in which the measurements were made. The $(1-\delta)$ determinations were then made of these materials under constant EBIC excitation. The need for constant excitation increased the difficulty of making accurate measurements, since the input current tended to drift and the measuring circuit had a relatively long time constant.

When EBIC excitation is used to obtain measurable target signal currents, it is necessary to correct the magnitude of the beam current so that it corresponds
to the beam current going to the excited areas only. For the measurements reported here, the ratio of the total scanned area to the excited area of the target was 4:1. In this report measurements of (1−6) in which the total beam current have been corrected to correspond to the actual beam landing on the excited areas are referred to as "actual" (1−6) measurements; whereas the uncorrected ones are referred to as "video" type measurement, since they are made under typical video conditions. Unless stipulated specifically otherwise, all measurements in this report are of the "video" type. The (1−6) values can be converted to actual readings by multiplying by 4.4. Similarly, when EBIC excitation is used to energize a given target, the "actual" beam current to the excited area can be obtained by dividing the indicated video beam current by 4.4.

Experimental $I_T$ vs $I_B$ curves for an As$_2$S$_2$ target (581AR1) are plotted in Fig. 6 for different constant EBIC excitation. The curves are quite similar in shape to the curves calculated in Fig. 4 on the basis of a surface having the (1−6) characteristics defined by eq. 22. As $I_B$ was reduced at higher levels of excitation the image polarity reversed showing that $(V_s)_{min}$, the minimum on the $\delta$ vs $\bar{V}_s$ curve, was being approached. The filled-in points on the curves indicate the presence of reversed polarity images. The apparent $\bar{V}_s$ and (1−6) values corresponding to the first reversed image on the $8 \times 10^{-14}$ ampere excitation curve can be obtained using eq. (2) as follows:

$$\bar{V}_s = 35.9 \text{ volts}$$
$$I_T = \frac{50 - \bar{V}_s}{8.3 \times 10^{-8}} = 1.7 \times 10^{-8}$$

The target resistance as a function of the EBIC excitation input current was calculated using eq. (11) for the 4 lower curves of Fig. 6 on the assumption that signal saturation as a function of beam current was obtained on these curves. The resulting values of target resistance under excitation have been plotted as the lower curve in Fig. 7 as a function of input current. Also shown in Fig. 7 are target resistance values for As$_2$S$_2$ targets under excitation as a function of input current, which were obtained in similar fashion. The excited area of the target was approximately 0.5 cm$^2$ in area. Thus the resistivity of the target material can be obtained at a given excitation by multiplying the computed resistance by $10^7/2d$, where $d$ is in microns. Since target 581AR1 was 1.6µ, this factor is equal to 3.1 x $10^3$. From separate data the dark resistance of the targets lies between $10^{15}$ to $10^{16}$ ohm-cms.

On the assumption that target resistance at a fixed value of excitation does not change as a result of the variation in target field gradients with change in beam current, (1−6) = $I_{m}/I_B$ has been calculated as a function of $\bar{V}_s$, where $\bar{V}_s$ is determined from the relationship $\bar{V}_s = V_T - I_T R$. The (1−6) values
Fig. 6—EBIC signal current for As$_2$S$_2$ target as function of input current (target 581 AR1, $V_I$ = 50 volts)
Fig. 7 - Resistance of As$_2$S$_3$ and As$_2$S$_2$ EBIC targets as function of input current.

- Target 581 AR1: $V_T = 50$ volts, As$_2$S$_2$
- Target 908: $V_T = 40$ volts, As$_2$S$_3$
- Target 909: $V_T = 40$ volts, As$_2$S$_3$

Where $I$ is the input current in amperes.
corresponding to input currents of $8 \times 10^{-11}$, $5 \times 10^{-11}$, and $10^{-11}$ amperes are plotted as a function of $V_s$ in Fig. 8. Reasonable agreement between the different curves may be observed in the region of low $V_s$. The upper curve can be approximated between the origin and 20 volts by a straight line having the equation $1-V_s = 1.25 \times 10^{-2} V_s$.

The knowledge of $V_s$ for various values of $I_B$ and $I$ is used in plotting Fig. 9. In this figure, $V_s$ is plotted as a function of $I$ for $I_B$ values of $10^{-6}$, $10^{-7}$ and $10^{-8}$ amperes respectively, assuming $a = 1.25 \times 10^{-2}$ volts$^{-1/2}$. It is pertinent to point out that once the constant $a$ has been evaluated, $V_s$ can be obtained very simply from a knowledge of $I_m$ using eq. (24), recognizing that this equation holds only in the region where the $(1-5)$ curve versus $V_s$ can be approximated by a straight line, i.e., between 0 and 20 volts.

The discrepancies in the $(1-5)$ values at high values of $V_s$ input excitation raises the question as to whether the differences in the measurements were due to non-ohmic behavior of the targets, to the influence of charge carriers, filled states, etc., within the forbidden band of the target material as a function of the excitation, or possibly to inaccuracy of measurements due to the factors described previously.

Accordingly, the series of measurements plotted in Fig. 10 for an As$_2$S$_2$ target were made at $10^{-10}$ and $3 \times 10^{-11}$ ampere input excitations. The readings were repeated several hours later with fairly good agreement being obtained. The measurements shown on the bottom curve of the figure were made at $2 \times 10^{-12}$ amperes input excitation. This curve indicates that an apparently real substantial diminution in the electron absorptivity of the target occurs at very low excitations. Evidently, the particular As$_2$S$_2$ target employed has a high reflectivity for electrons when charge carriers are not present. The presence of charge carriers or some effect associated with the presence of charge carriers greatly increases the probability of capture of low velocity electrons.

A similar series of measurements were taken on another As$_2$S$_2$ target (9291AR3). In these tests, an attempt was also made to observe the effect on the target of overnight exposure to the atmosphere of the demountable position. The solid curves of Fig. 11 give $I_m$ as a function of $I_B$ for $4 \times 10^{-11}$, $10^{-11}$ and $4 \times 10^{-12}$ amperes input excitation. The dotted curves give the $I_T$ vs $I_B$ characteristic, as taken after overnight exposure in the demountable position, at $4 \times 10^{-11}$ and $10^{-11}$ ampere levels of excitation. In general, the effect of the overnight exposure appears to be to lower the saturated signal levels somewhat, which is equivalent to lowering target gain, and to extend the saturated current plateau, which now occurs over a wider range of $I_B$ values.

The $(1-5)$ curves, before and after overnight exposure in the demountable, are plotted in Figs. 12 and 13 respectively. It is interesting to note in Fig. 12 that the $(1-5)$ values for $4 \times 10^{-11}$ and $10^{-11}$ ampere input excitations show the same marked increase with input excitation as was observed in the data of Fig. 10.
Fig. 8 - Plot of \( \alpha - \delta \) as function of \( \bar{V}_S \) for As\(_2\)S\(_2\) target (target 581 AR1, \( V_T = 50 \) volts)
Fig. 9—Target surface potential $\bar{V}_s$ as function of input current for $As_2S_2$ target and different values of beam current.
Fig. 10—Plot of (I-\bar{I}) under imaging conditions as function of \bar{V}_S for As_3S_2 target.
Fig. 11—EBIC signal current for $\text{As}_2\text{S}_2$ target as function of $I_B$ for different values of input current.
Fig. 12—Plot of ($1 - \bar{\delta}$) under imaging conditions as function of $\bar{V}_s$ for $\text{As}_2\text{S}_2$ target.
Fig. 13 — Plot of (1-\(\overline{\delta}\)) under imaging conditions as function of \(\overline{V}_S\) for As$_2$S$_2$ target after overnight exposure in demountable.
However, the electron absorptivity curve at $4 \times 10^{-12}$ ampere excitation level appears to switch from a low level to a high level of electron absorptivity while the measurements were being made.

Ordinarily, the input excitation was energized on an intermittent basis, and was interrupted as soon as a given measurement was made. A repeat $4 \times 10^{-11}$ ampere curve was taken with the excitation on continuously. This curve is also shown in Fig. 11. The corresponding electron absorptivity curve, which is shown in Fig. 13, is characterized by an unusual flat response.

The (1-5) characteristic for an As$_2$S$_3$ target (909) are given in Fig. 14 for different excitations. Two points are also given for a separate As$_2$S$_3$ target. Sufficient data have not been taken to date so as to afford a reliable criteria for assessing the electron absorptivity of As$_2$S$_3$ versus As$_2$S$_2$. It may well be that the variation between individual targets will turn out to be large compared to the average difference in characteristics. There seems to be some indication that As$_2$S$_3$ has a higher reflectivity for low velocity electrons.

Fig. 15 gives the (1-5) characteristics for an As$_2$S$_2$ and an As$_2$S$_3$ target having an overlayer of 0.2 microns of Sb$_2$S$_3$. There is some indication that the overlayer has not significantly affected the electron absorptivity of the surfaces, which appear to be determined by the substrates beneath the Sb$_2$S$_3$ films.

The (1-5) characteristics of an As$_2$S$_3$ target having a relatively thick overlay of Sb$_2$S$_3$ (0.5 µ) is shown in Fig. 16. Here a substantial change in electron absorptivity with change in input excitation is noted. The curve with $3 \times 10^{-10}$ ampere input has the highest electron absorptivity. The (1-5) corresponding to $10^{-10}$ ampere excitation is significantly lower. The $10^{-11}$ ampere curve has the lowest (1-5) values on the curve. It is interesting to note that a reversal apparently takes place, with the $5 \times 10^{-12}$ ampere curve falling between the $10^{-11}$ ampere and the $10^{-10}$ ampere curves. A similar reversal took place on Fig. 8, where the electron absorptivity corresponding to an $8 \times 10^{-11}$ ampere input is somewhat lower than the 1-5 corresponding to a $5 \times 10^{-11}$ ampere input excitation.

The effect of evaporating an Sb$_2$S$_3$ overlay 0.5 microns in thickness had no effect on the electron absorptivity of As$_2$Se$_3$ at $10^{-11}$ ampere excitation. Curves taken before and after excitation are shown in Fig. 17. However, increase in excitation to $3 \times 10^{-10}$ amperes produced a substantial increase in the (1-5) characteristic as indicated by the upper curve of the figure after evaporating of the Sb$_2$S$_3$ overlay.

For purposes of comparison, the (1-5) characteristic was taken of a standard commercial Sb$_2$S$_3$ vidicon tube. Since the entire scanned raster area was illuminated, the (1-5) values in Fig. 18 are "actual". From the data taken, it would appear as if the $V_s$ corresponds to the first crossover would be in the neighborhood of 17 to 18 volts which is substantially lower than observed values.
Target 909, 1.5 microns thick
- $I_i > 10^{-9}$ amps (Used for curve)
- $I_i > 5 \times 10^{-11}$ amps, $V_T = 40$ volts
- $I_i > 10^{-11}$ amps

Target 891AR5, 1.5 microns thick
- $I_i = 3 \times 10^{-11}$ amps, $V_T = 35$ volts

Fig.14—Plot of $1 - \bar{\delta}$ as function of $\bar{V}_s$ for $\text{As}_2\text{S}_3$ targets
Fig. 15—Plot of \(1 - \delta\) as function of \(\bar{V}_s\) for EBIC targets with vacuum evaporated overlayer of \(\text{Sb}_2\text{S}_3\).
Fig. 16—Plot of (1-δ) as function of $\bar{V}_S$ for $\text{As}_2\text{S}_2$ with $\text{Sb}_2\text{S}_3$ vacuum evaporated overlayer.

Target 581ARZ, 1.6 μ $\text{As}_2\text{S}_2$ with .5 μ of vacuum evaporated $\text{Sb}_2\text{S}_3$, $V_T$=70 volts

- $I_i = 5 \times 10^{-12}$ amps
- $I_i' = 10^{-11}$ amps
- $I_i'' = 10^{-10}$ amps
- $I_i''' = 3 \times 10^{-10}$ amps
Target 5191AR1 1.3 μ thick with and without overlay of 0.5 μ of vacuum evaporated Sb$_2$S$_3$

- Without Sb$_2$S$_3$: $I_s = 10^{-11}$ amps, $V_T = 40$ V
- With Sb$_2$S$_3$: $I_s = 3 \times 10^{-10}$ amps, $V_T = 30$ V
- With Sb$_2$S$_3$: $I_s = 10^{-11}$ amps, $V_T = 30$ V

Fig. 17 - Plot of $(I-\delta)$ as function of $\bar{V}_s$ for As$_2$Se$_3$ EBIC target
Fig. 18—Plot of $1 - \bar{d}$ as function of $\bar{V}_s$ for vidicon tube, $V_T = 16$ volts
for arsenic sulphides. It is interesting to note that the (1-5) value corresponding to a low input illumination was very low, again indicating very high reflectivity for low velocity electrons at low values of excitation.

In general, the first crossover potential for As$_2$S$_3$ and As$_2$S$_2$ has usually been between 50 and 90 volts. One of the techniques for determining the first crossover potential has involved exposing the target to a bright light with the beam off at a given test value of backplate potential. The scan beam is then energized suddenly, and the video pattern on the monitor observed to determine whether any parts of the raster have gone over the first crossover potential. By extrapolation, the curves of Figs. 10, 12, 13, 14, and 15 appear to have first crossover potential in the range determined by these independent monitor observations.

It is interesting to note that the deposition of relatively thick layers of Sb$_2$S$_3$ over the arsenic sulphides have not significantly affected the first crossover potential, which is apparently determined by the characteristics of the substrate layers.

Evidently it would be possible to obtain a video image from the target of Fig. 16, even if all parts of the target surface were at a common value of $V$. The state of excitation of the target acts in a manner similar to a grid, essentially reflecting electrons from dark areas of the target, and interfering with the reflection, i.e., absorbing more of the electrons which are attempting to leave signal areas, in proportion to the signal excitation. It is this mode of image which was referred to previously as charge carrier beam modulation imaging.

Curves of $I_m$ versus $V_m$ for an As$_2$S$_2$ target (91S1AR2) have been plotted in Fig. 19 for input excitations of $3 \times 10^{-11}$, $10^{-11}$, and $3 \times 10^{-12}$ amperes. It is important to know in interpreting the results whether the curve corresponding to $3 \times 10^{-11}$ amperes input represents saturated values of beam input current. $I_m$ versus $I_B$ curves taken at $V_T = 20$ and 50 volts have established that the $3 \times 10^{-11}$ amper input excitation curve represents saturated values of $I_T$ in the $I_T$ vs $I_B$ curve to backplate potentials of at least 50 volts.

From these curves it is evident that the approximation made by assuming that the target responds ohmically (i.e., would exhibit a linear response in Fig. 19) introduces no very great error for As$_2$S$_2$ targets having up to 50 volts impressed across them.

The signal current curves of Fig. 19 which correspond to $3 \times 10^{-11}$ and $10^{-11}$ ampere excitations vary with 1.1 and 1.5 power respectively of the applied backplate voltage. The upper part of the $3 \times 10^{-12}$ ampere excitation curves varies with the 3.2 power of the backplate potential. The characteristics of the target of Fig. 19 fall into the general pattern described by Lampert, Ref. 7, for an insulator with traps. The higher than unity power variation of $I_T$ vs $V_T$ is due to an increase in Fermi level of the solid as the trapping states get filled. Further confirmation that the $I_T$ vs $V_T$ characteristics are affected by the presence of traps are the high transient signals noted when target voltage is suddenly increased during EBIC excitation. Similar transients have been noted in CdS
Fig. 19 - $I_T$ versus $V_T$ for $I_B = 10^{-6}$ Amp. and different input currents.
crystals by Smith and Rose, Ref. 8. These authors explain the transients as due to surges of charge carriers which are injected into the insulator from the contacts and which are capable of passing relatively high currents before a good portion of the excess charge gets trapped. The presence of filled traps increases the density of space charge within the solid, thereby limiting the flow of charge to steady state values which are very small compared to the steady state currents attainable in a trap-free solid.

Similar curves to those of Fig. 19 are plotted in Fig. 20 using a factor of 10 lower beam. The beam employed is not large enough to insure signal current saturation at the higher signal current levels, and the secondary emission characteristics of the target play a significant role in determining the shape of these curves. The $10^{-11}$ and $3 \times 10^{-12}$ amperes input curves are higher at low values of $V_T$ than the corresponding curves for the higher beam. This may be due to a change of characteristics of the material with continued excitation or to experimental difficulties.

The effect of beam current level on the $I_T$ vs $I_i$ characteristics of an As$_2$S$_2$ target are shown in Fig. 21. A similar plot on a log-log scale is given in Fig. 22 for a separate, somewhat thicker, As$_2$S$_2$ target. The curve corresponding to the highest value of beam in this figure has a 0.9 power variation of signal current relative to input current.

It is interesting to note that the curves corresponding to the lower value of beam currents rise to maximum values and then start to decrease. It would appear that these maxima do not correspond to space charge limited current saturation values but rather are ascribable to values of $V_S$ which have exceeded the maxima on the curves of $V_S$ vs $(1-5)$.

c. Discussion on Electron Absorptivity of Insulators

Unless energy absorbing collisions occur within an insulator, one would expect that low velocity electrons impinging on a surface will eventually experience a series of elastic reflections which will cause them eventually to leave the solid. Further, it would be necessary, if the electrons are to be retained within the solid in the case in inelastic collisions, that they lose enough energy per collision so that they do not have enough energy to overcome the electron affinity of the surface should they reach the surface in the course of their motion. Since the mechanisms of energy loss for secondary electrons leaving an insulator from a site a number of hundred Angstroms beneath the surface have much in common with energy losses experienced by low velocity scan electrons entering the material, the energy losses experienced by secondary electrons which originate within the volume of a material on their way out of the solid are very pertinent to the problem at hand.

The high secondary emission yield from insulators has been explained, Ref. 9, as due to an increased depth of escape of secondary electrons. The larger
Fig. 20 - $I_T$ versus $V_T$ for $I_B = 10^{-7}$ Amp. and different input currents.
Fig. 21 - Target signal vs. input current for different values of $I_B$ and $V_T = 50$ volts

Target 9181 AR2 2μ As$_2$S$_2$

- $I_B = 6 \times 10^{-7}$ Amp.
- $I_B = 2.4 \times 10^{-7}$ Amp.
- $I_B = 1.8 \times 10^{-7}$ Amp.
- $I_B = 1.2 \times 10^{-7}$ Amp.
Fig. 22 — Target signal vs. input current for different values of $I_B$ and $V_T = 50$ volts.
mean free path for electrons in an insulator is attributable to a lower probability for collisions which involve energy losses.

One of the commonly held theories of secondary emission from metals holds that the secondaries which are released within the volume lose their energy rapidly by interaction with the conduction electrons. This mechanism for absorption of energy from electrons does not occur within insulators because of the low density of charge carriers. The following are the three principle mechanisms, Ref. 9, for absorption of energy from low energy electrons by insulators: (1) electron-phonon interaction, i.e., interaction with lattice vibrations, (2) interaction with valence electrons, i.e., creation of electron hole pairs, and (3) interaction with lattice defects.

Dekker, Ref. 10, has estimated the depth of escape of secondaries from Pt, Ge, and MgO as corresponding to 20, 35, and 230 Å respectively. Haxby, Ref. 11, has experimentally determined that secondary electrons can be released in MgO films from depths of the order of 400 Å. The depths cited above for insulators are very low compared to the thickness of SbS₅ overlays discussed in the previous section.

The salient question as to the distances which can be traversed by electrons in an insulator of course has to do with the mechanism for absorption of energy of the electron within the insulator in question. If the electron has insufficient energy to produce band-to-band transitions, then it would appear that relatively large ranges are possible with certain materials. In work on selenium, Ref. 4, 16, it has been demonstrated that the range of carriers can be of the order of 5 to 10 microns. Similarly, it has been possible to obtain relatively high EBIC gains in As₂S₂ films which are of the order of 4 μ thick. Since the primary electrons are absorbed in less than 2 μ of thickness, it is evident that the range of carriers is at least of the order of 2 μ for As₂S₂. In order for the electrons to escape from the material, they must reach the surface with sufficient energy to overcome the electron affinity of the surface, which conceivably could be as low as 0.5 ev, and even lower.

Several experiments, Ref. 12, 13, have demonstrated that electrons can be trapped in KCl films and then released by bombarding electrons having initial energies in the same range as the equivalent photon interactions, Ref. 14. Jacobs, Martin, and Brand, Ref. 14, working on composite surfaces have concluded that true secondaries originate from the filled band, i.e., transitions across the band gap of the insulator, rather than from traps.

These experimenters, Ref. 14, show experimental curves in the range between 0 and 20 ev which are relevant to the measurements made in the previous section. For an AgCsO film, the secondary emission ratio for primaries between 2 and 10 ev is of the order of .96 to .98, corresponding to "actual" (1-5) of the order of .02 to .04. The secondary emission ratio of KCl dips to a minimum of .955 at 9 ev. Both of these materials show the very high electron reflectivity for low velocity electrons noted in the previous section. In general the
threshold values for secondary emission check closely with the optical energies required to remove an electron from the filled band into the vacuum.

Fredericks and Cook, Ref. 15, in similar measurements on KCl have determined electron absorptivity values between .2 and .3 in the range of electron energies between 1 and 10 ev. Somewhat lower absorptions were determined for KBr. The KCl absorptivity data are in disagreement with the work of Ref. 14.

Referring to the change in (1-5) as a function of input excitation observed in the previous section, it is likely that this effect can be explained on the basis of increased opportunities for the absorption of the energy of low velocity electrons by electrons in filled traps rather than by direct interaction with the charge carriers. Further careful measurements are required to help understand the mechanism, and to determine the applicability of the effect to the imaging problems at hand.

4) Survey of EBIC Target Materials*  

a. Arsenic Compounds of the $M_2^{VA, VIB}$ Family  

Table II summarizes the EBIC characteristics of a number of different formulations of As, Se, and S, as substituted in the basic As$_2$S$_3$ and As$_2$Se$_3$ stoichiometry. From this table it is evident that the EBIC gain tends to increase as the percentage of selenium employed in the material increases. Vacuum baking of the experimental targets for 2 hrs at 100°C did not produce very substantial changes in the EBIC gain. The vacuum bakes did substantially decrease the persistence of the As$_2$Se$_2$S and As$_2$SeS$_2$ targets, and tended to increase the number of bright spots in the dark current image.

In the preliminary tests most of these materials exhibited an ohmic variation of signal current with target voltage and a first power variation of output with input current at low target voltages. Persistence at a given target voltage was proportional to the duration and magnitude of the excitation current. The persistence of As$_2$Se$_2$S targets generally increased with target voltage, whereas most of the other materials listed in Table II either exhibited small change in persistence with change in target voltage, or the persistence decreased with increasing target voltage.

In general, the ability to operate at high target voltages was limited by the appearance of a large array of target spots as target voltage was increased, and by the tendency of the surface to go over the first crossover potential.

The formulation As$_2$Te$_2$S was also tested. No EBIC image was obtained.

* Most of the special materials were made in the Semiconductor Department under the guidance of Dr. A. Cornish.
<table>
<thead>
<tr>
<th>Target No.</th>
<th>Mat.</th>
<th>Approx. Thickness (Microns)</th>
<th>Gain</th>
<th>$V_T$</th>
<th>Persistence</th>
</tr>
</thead>
<tbody>
<tr>
<td>L630</td>
<td>As$_2$Se$_2$S</td>
<td>3</td>
<td>1200</td>
<td>40</td>
<td>15</td>
</tr>
<tr>
<td>L633</td>
<td>&quot;</td>
<td>3</td>
<td>600</td>
<td>40</td>
<td>4</td>
</tr>
<tr>
<td>L636</td>
<td>&quot;</td>
<td>1.7</td>
<td>1050</td>
<td>50</td>
<td>long</td>
</tr>
<tr>
<td>L637</td>
<td>&quot;</td>
<td>1.7</td>
<td>700</td>
<td>40</td>
<td>5</td>
</tr>
<tr>
<td>L635</td>
<td>&quot;</td>
<td>1.7</td>
<td>500</td>
<td>40</td>
<td>long</td>
</tr>
<tr>
<td></td>
<td></td>
<td>(after 2 hr 100°C bake)</td>
<td>800</td>
<td>30</td>
<td>3</td>
</tr>
<tr>
<td>L638</td>
<td>As$_2$Se$_2$S</td>
<td>2.2</td>
<td>900</td>
<td>40</td>
<td>long</td>
</tr>
<tr>
<td></td>
<td></td>
<td>(after 2 hr 100°C bake)</td>
<td>800</td>
<td>40</td>
<td>4</td>
</tr>
<tr>
<td>L639</td>
<td>As$_2$Se$_2$S</td>
<td>2.2</td>
<td>700</td>
<td>50</td>
<td>15</td>
</tr>
<tr>
<td></td>
<td></td>
<td>(after 2 hr 100°C bake)</td>
<td>600</td>
<td>40</td>
<td>4</td>
</tr>
<tr>
<td>L640</td>
<td>As$_2$Se$_2$S</td>
<td>2.2</td>
<td>400</td>
<td>30</td>
<td>7</td>
</tr>
<tr>
<td></td>
<td></td>
<td>(after 2 hr 100°C bake)</td>
<td>500</td>
<td>40</td>
<td>5</td>
</tr>
<tr>
<td>L641</td>
<td>As$_2$Se$_2$S</td>
<td>1.7</td>
<td>900</td>
<td>50</td>
<td>4</td>
</tr>
<tr>
<td>L643</td>
<td>&quot;</td>
<td>1.7</td>
<td>900</td>
<td>50</td>
<td>long</td>
</tr>
<tr>
<td></td>
<td></td>
<td>(after 2 hr 100°C bake)</td>
<td>600</td>
<td>40</td>
<td>6</td>
</tr>
<tr>
<td>L688</td>
<td>As$<em>2$Se$</em>{2.5}$S$_{0.5}$</td>
<td>2.6</td>
<td>1000</td>
<td>30</td>
<td>3</td>
</tr>
<tr>
<td>L689</td>
<td>&quot;</td>
<td>2.6</td>
<td>1500</td>
<td>40</td>
<td>1</td>
</tr>
<tr>
<td>L690</td>
<td>&quot;</td>
<td>2.6</td>
<td>900</td>
<td>30</td>
<td>4</td>
</tr>
<tr>
<td>L692</td>
<td>As$<em>2$Se$</em>{1.5}$S$_{1.5}$</td>
<td>3.5</td>
<td>800</td>
<td>50</td>
<td>5</td>
</tr>
<tr>
<td>L694</td>
<td>&quot;</td>
<td>3.5</td>
<td>500</td>
<td>40</td>
<td>4</td>
</tr>
<tr>
<td>L695</td>
<td>&quot;</td>
<td>3.5</td>
<td>700</td>
<td>50</td>
<td>2</td>
</tr>
</tbody>
</table>
Preliminary tests on non-stoichiometric formulations of As, Se, and S are shown in Table III. These materials have tended to be more persistent than the materials listed in Table II. All of these materials increased in persistence as a function of backplate potential.

A two section evaporation of Sb\(_2\)S\(_3\) was superimposed on target L773. One-third of the area of the target consisted of an As\(_2\)Se\(_2\)S\(_{0.5}\) film having about a 1 \(\mu\) layer of Sb\(_2\)S\(_3\) over it, a second area had a .5 \(\mu\) coating of Sb\(_2\)S\(_3\) evaporated onto it. The remaining area of As\(_2\)Se\(_2\)S\(_{0.5}\) was shielded from the Sb\(_2\)S\(_3\) layer during the evaporation. As the target backplate voltage was increased, target bright spots first showed up in the area which had been shielded from Sb\(_2\)S\(_3\) during the evaporation. This area was also the first area which exhibited first crossover difficulties. In general there appeared to be no advantage associated with the use of targets having off-stoichiometric formulations.

The substitution of oxygen for one of the sulphur or selenium atoms in the As\(_2\)S\(_3\) stoichiometry tended to lower the EBIC gain somewhat. Such targets were also limited in the backplate potentials at which they could be operated by the presence of bright spots. Results on these targets are summarized in Table IV. Also shown in this table are test results on two formulations in which one arsenic atom is replaced by an Sb atom. Gains in both AsSbS\(_3\) and AsSbSe\(_2\) were lower than most of the other formulations summarized in Tables II, III, and IV.

b. Ternary Formulations Incorporating As and Se

Certain metals of the IIB group of the periodic table form compounds with Se and S such as ZnSe and CdS, which are stable at high temperatures and which have low vapor pressures. These materials are capable, when properly activated, of giving good photoconductive response. For this reason it appeared to be appropriate to investigate whether ternary materials incorporating Se and As and metals such as Zn and Cd would have useful EBIC characteristics as well as better stability with temperature.

Test results on CdAs\(_2\)Se\(_4\), which are summarized in Table V, indicate capabilities of high EBIC gains at relatively low values of target backplate voltages. Persistences were initially excessive, but decreased when the material was vacuum baked for 2 hrs at 100\(^\circ\)C. Substantially higher filament currents were required to evaporate the CdAs\(_2\)Se\(_4\) material. In view of some evidence of decomposition during evaporation, a chemical analysis of the evaporated film was made. The ratio of Se to As exactly corresponded to that expected from As\(_2\)Se\(_3\). The indications are that the following reaction takes place under vacuum when the temperature gets sufficiently high:

\[
\text{CdAs}_2\text{Se}_4 \xrightarrow{\text{vacuum}} \text{CdSe} + \text{As}_2\text{Se}_3
\]

Since the CdSe has a low vapor pressure, relatively little of it would be expected to reach the EBIC film.
<table>
<thead>
<tr>
<th>Target No.</th>
<th>Mat.</th>
<th>Approx. Thickness (Microns)</th>
<th>Gain</th>
<th>VT</th>
<th>Persistence</th>
</tr>
</thead>
<tbody>
<tr>
<td>L763</td>
<td>As$<em>2$Se$</em>{1.5}$S</td>
<td>2.5</td>
<td>1300</td>
<td>50</td>
<td>60 long</td>
</tr>
<tr>
<td>L767</td>
<td>As$_{1.5}$S$_2$S</td>
<td>1.3</td>
<td>700</td>
<td>50</td>
<td>long</td>
</tr>
<tr>
<td>L768</td>
<td>&quot;</td>
<td>1.3</td>
<td>800</td>
<td>40</td>
<td>5</td>
</tr>
<tr>
<td>L773</td>
<td>As$<em>2$Se$</em>{2.0}$S</td>
<td>1.4</td>
<td>1100</td>
<td>50</td>
<td>long</td>
</tr>
</tbody>
</table>

*after evaporation of a Sb$_2$S$_3$ double layer*

<table>
<thead>
<tr>
<th>Seconds Persistence</th>
<th>High Level</th>
<th>Low Level</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td>2200</td>
<td>75</td>
</tr>
<tr>
<td></td>
<td>1000</td>
<td>30</td>
</tr>
</tbody>
</table>

-46-
<table>
<thead>
<tr>
<th>Target No.</th>
<th>Mat.</th>
<th>Approx. Thickness (Microns)</th>
<th>Gain</th>
<th>VT</th>
<th>High Level</th>
<th>Low Level</th>
</tr>
</thead>
<tbody>
<tr>
<td>L710</td>
<td>As$_2$S$_2$O</td>
<td>1</td>
<td>400</td>
<td>50</td>
<td>2</td>
<td>12</td>
</tr>
<tr>
<td>L746</td>
<td></td>
<td>2.5</td>
<td>200</td>
<td>50</td>
<td>3</td>
<td>25</td>
</tr>
<tr>
<td>L704</td>
<td>As$_2$SeS0</td>
<td>1.1</td>
<td>100</td>
<td>20</td>
<td>22</td>
<td>long</td>
</tr>
<tr>
<td>L705</td>
<td></td>
<td>1.1</td>
<td>400</td>
<td>30</td>
<td>3</td>
<td></td>
</tr>
<tr>
<td>L706</td>
<td></td>
<td>1.1</td>
<td>400</td>
<td>30</td>
<td>2</td>
<td></td>
</tr>
<tr>
<td>L750</td>
<td></td>
<td>1.5</td>
<td>400</td>
<td>30</td>
<td>9</td>
<td></td>
</tr>
<tr>
<td>L755</td>
<td>AsSbS$_3$</td>
<td>.07</td>
<td></td>
<td></td>
<td>(no image or gain)</td>
<td></td>
</tr>
<tr>
<td>L758</td>
<td></td>
<td>.8</td>
<td>330</td>
<td>40</td>
<td>long</td>
<td></td>
</tr>
<tr>
<td>L761</td>
<td>AsSbSe$_3$</td>
<td>.05</td>
<td>270</td>
<td>20</td>
<td>4</td>
<td>25</td>
</tr>
<tr>
<td>L782</td>
<td></td>
<td>1.3</td>
<td></td>
<td></td>
<td>(no image)</td>
<td></td>
</tr>
</tbody>
</table>

**TABLE IV**

EBIC CHARACTERISTICS OF SOME SPECIAL FORMULATIONS OF As, Se, S AND O
<table>
<thead>
<tr>
<th>Target No.</th>
<th>Mat.</th>
<th>Est. ug/cm²</th>
<th>Gain</th>
<th>( V_T )</th>
<th>High Level Persistence</th>
<th>Low Level Persistence</th>
</tr>
</thead>
<tbody>
<tr>
<td>L855</td>
<td>CdAs(_2)Se(_4)</td>
<td>330</td>
<td>600</td>
<td>20</td>
<td>long</td>
<td></td>
</tr>
<tr>
<td>L864</td>
<td>&quot;</td>
<td>615</td>
<td>1700</td>
<td>30</td>
<td>&quot;</td>
<td></td>
</tr>
<tr>
<td>L865</td>
<td>&quot;</td>
<td>615</td>
<td>650</td>
<td>15</td>
<td>long</td>
<td>&quot;</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>1500</td>
<td>35</td>
<td>&quot;</td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td>After 2 hr 100°C bake</td>
<td>1000 40 1</td>
</tr>
<tr>
<td>L866</td>
<td>&quot;</td>
<td>615</td>
<td>400</td>
<td>8</td>
<td>1/2</td>
<td>60</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>700</td>
<td>15</td>
<td>long</td>
<td></td>
</tr>
<tr>
<td>L868</td>
<td>&quot;</td>
<td>615</td>
<td>1000</td>
<td>8</td>
<td>long</td>
<td></td>
</tr>
<tr>
<td>L929</td>
<td>(In substrate)</td>
<td></td>
<td>1666</td>
<td>50</td>
<td>1/2</td>
<td>30</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td>After 2 hr 100°C bake</td>
<td>&quot;</td>
</tr>
<tr>
<td>4271AR2</td>
<td>&quot;</td>
<td>254</td>
<td>200</td>
<td>10</td>
<td>2</td>
<td></td>
</tr>
<tr>
<td>4271AR6</td>
<td>&quot;</td>
<td>254</td>
<td>500</td>
<td>20</td>
<td>1/2</td>
<td></td>
</tr>
<tr>
<td>4251AR1</td>
<td>&quot;</td>
<td>351</td>
<td>500</td>
<td>25</td>
<td>long</td>
<td></td>
</tr>
<tr>
<td>L928</td>
<td>&quot;</td>
<td>1000</td>
<td>1250</td>
<td>40</td>
<td>long</td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td>After 2 hr 100°C</td>
<td>1200 30 1</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td>(add 105 ug/cm² Sb(_2)S(_3))</td>
<td>2200 40 1/2</td>
</tr>
</tbody>
</table>
The highest gain using the CdAs$_2$Se$_4$ material was observed on a baked film (L928) after approximately a .2 $\mu$ layer of Sb$_2$S$_3$ was evaporated over it. A gain of 2200 was observed at 40 volts.

Test results on several other ternary materials are summarized in Table VI. AgAsSe$_2$ exhibited low gain at low target thickness, but improved with thickness. Targets fabricated of ZnIn$_2$Se$_4$ were capable of reverse polarity images only, whereas targets fabricated of ZnAs$_2$Se$_4$, CdAs$_2$Se$_7$ and HgAs$_2$Se$_4$ had promising gains. The AgAsSe$_2$ material revealed only a trace of Ag present in the evaporated target according to spectrographic tests. The indications are that the target materials resulting from the evaporation of the materials in Table VI are probably largely As$_2$Se$_3$ with some impurities present.

The type of substrates used appears to be of considerable importance with some of the materials employed. All of the targets listed in Table V made use of Al substrates which were evaporated onto Al$_2$O$_3$ self-supporting layers as described in Ref. 1, with the exception of target L828 which made use of an In substrate. Several CdAs$_2$Se$_4$ targets, not listed in the table, which were evaporated onto gold substrates exhibited no gain although some imaging was possible.

Similar results were observed in the tests on AgAsSe$_2$ targets. When 115 $\mu$g/cm$^2$ of this material was evaporated onto 3 targets having indium, gold, and platinum substrates, these targets were incapable of imaging even through companion targets having Al substrates and subject to the same evaporation, did exhibit gain and imaging capabilities. The evaporation of a second layer of AgAsSe$_2$ improved the target with the gold substrate to the extent that a gain of 670 was obtained at 5 target volts. The platinum substrate target which was also subjected to a second evaporation was still incapable of imaging.

c. Summary of Sb$_2$S$_3$ Type Materials

Tests on Sb$_2$S$_3$ type materials are summarized in Table VII. In general, Sb$_2$S$_3$ targets exhibit higher gain under reverse polarity scan conditions. Targets in which the initial material was 50% Sb$_2$S$_3$ and 50% As$_2$S$_3$ have promising gains under conditions of normal polarity scan. Both Sb$_2$S$_2$O$_2$ and Sb$_2$S$_2$O also appear to be promising in terms of the gains observed at low target voltages.

By the use of a rotatable shield it was possible to evaporate the Sb$_2$S$_3$ on target L791 in layers having 3 different thicknesses varying from .3 $\mu$ for the thinnest, to .7 $\mu$ for the intermediate layer, and 1.2 $\mu$ for the thickest evaporation. In general the .3 $\mu$ section was usable at low target voltages only. The 1.2 $\mu$ thick area had the best EBIC performance from the standpoint of imaging at the low input currents. This layer also had less bright spots at a given target voltage.

Several Sb$_2$Se$_3$ targets were also checked. No gain was observed, apparently because of the high conductivity of this material.
# Table VI

## EBIC Characteristics of Ternary Materials Incorporating Selenium

<table>
<thead>
<tr>
<th>Target No.</th>
<th>Mat.</th>
<th>Est. p ug/cm²</th>
<th>Gain</th>
<th>VT</th>
<th>Persistence</th>
</tr>
</thead>
<tbody>
<tr>
<td>L842</td>
<td>AgAsSe₂</td>
<td>283</td>
<td>500</td>
<td>20</td>
<td>High</td>
</tr>
<tr>
<td>L849</td>
<td>&quot;</td>
<td>115</td>
<td>250</td>
<td>10</td>
<td>Low</td>
</tr>
<tr>
<td>L850</td>
<td>&quot;</td>
<td>115</td>
<td>175</td>
<td>20</td>
<td>Low</td>
</tr>
<tr>
<td>L851</td>
<td>&quot;</td>
<td>115</td>
<td>166</td>
<td>10</td>
<td>Low</td>
</tr>
<tr>
<td>L857</td>
<td>&quot; approx. (500)</td>
<td>1000</td>
<td>20</td>
<td></td>
<td>Long</td>
</tr>
<tr>
<td>L822</td>
<td>ZnIn₂Se₄</td>
<td>210</td>
<td>(dim reverse polarity image)</td>
<td></td>
<td></td>
</tr>
<tr>
<td>L915</td>
<td>ZnAs₂Se₄</td>
<td>367</td>
<td>320</td>
<td>20</td>
<td>3</td>
</tr>
<tr>
<td>L996</td>
<td>Cd₄As₇Se₇</td>
<td>323</td>
<td>500</td>
<td>20</td>
<td>1</td>
</tr>
<tr>
<td>L998</td>
<td>&quot;</td>
<td>323</td>
<td>500</td>
<td>20</td>
<td>10</td>
</tr>
<tr>
<td>4211AR1</td>
<td>HgAs₂Se₄</td>
<td>238</td>
<td>500</td>
<td>20</td>
<td>15</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
</tbody>
</table>
TABLE VII
EBIC CHARACTERISTICS OF $\text{Sb}_2\text{S}_3$ TYPE MATERIALS

<table>
<thead>
<tr>
<th>Target No.</th>
<th>Mat.</th>
<th>Est. $\mu g/cm^2$</th>
<th>Gain</th>
<th>$V_T$</th>
<th>Seconds Persistence</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td>High Level</td>
</tr>
<tr>
<td>L342</td>
<td>Sb$_2$S$_3$</td>
<td>730</td>
<td>40</td>
<td>10</td>
<td>13</td>
</tr>
<tr>
<td>L344</td>
<td>&quot;</td>
<td>730</td>
<td>500</td>
<td>190*</td>
<td>9</td>
</tr>
<tr>
<td>L791</td>
<td>Sb$_2$S$_3$ Triple Layer</td>
<td>300</td>
<td>10</td>
<td>30-200</td>
<td>5</td>
</tr>
<tr>
<td>L901</td>
<td>&quot;</td>
<td>420</td>
<td>no gain</td>
<td>no gain</td>
<td>no gain</td>
</tr>
<tr>
<td>L950</td>
<td>1/2 Sb$_2$S$_3$</td>
<td>330</td>
<td>575</td>
<td>40</td>
<td>1</td>
</tr>
<tr>
<td>L951</td>
<td>1/2 As$_2$S$_3$ (after 2 hr 100°C)</td>
<td>470</td>
<td>50</td>
<td>1/2</td>
<td>8</td>
</tr>
<tr>
<td>L953</td>
<td>&quot;</td>
<td>330</td>
<td>750</td>
<td>50</td>
<td>1/2</td>
</tr>
<tr>
<td>L879</td>
<td>Sb$_2$S$_2$</td>
<td>413</td>
<td>500</td>
<td>15</td>
<td>long</td>
</tr>
<tr>
<td>L881</td>
<td>Sb$_2$S$_2^0$</td>
<td>300</td>
<td>100</td>
<td>8</td>
<td>11</td>
</tr>
</tbody>
</table>

*Reverse Polarity Scan
d. Alkali Halides

Several alkali halide materials not previously investigated have been tested. NaCl, LiI, and KBr did not demonstrate appreciable gain, although these materials evidenced the capability for EBIC imaging. Experimental NaI and KI targets without thallium activators exhibited approximately the same performance.

e. Miscellaneous Materials

1. Cd$_3$As$_4$Se$_6$As$_2$O$_3$

Several targets were fabricated of this material. In general the targets were too thin for good performance (175 ug/cm$^2$). However, a gain of 250 at 10 volts was obtained on one of the targets.

2. GaP, Al$_2$Te$_3$ and Ga$_2$Se$_3$

The band gaps of GaP, Al$_2$Te$_3$ and Ga$_2$Se$_3$ are 2.24 ev, 2.5 ev, and 1.9 ev respectively. A 60 ug/cm$^2$ film of GaP gave no indication of light or EBIC sensitivity.

An Al$_2$Te$_3$ target about 80 ug/cm$^2$ in thickness exhibited no EBIC or light sensitivity, whereas a dim EBIC image was obtainable on a second target of the same thickness at target voltages which could be varied from 2 to 200 volts.

A 460 ug/cm$^2$ thickness of Ga$_2$Se$_3$ evidenced good light sensitivities. A dim EBIC image of normal polarity image could then be seen to 200 target volts.

5) Tube Program

a. Introduction

Four tubes have been manufactured under this contract. A summary of the details of these tubes is given in Table VIII. As pointed out in this table, all tubes feature vidicon scan, that is, a vidicon gun with direct target readout. Both electrostatic and magnetic image sections are used. Tubes having a magnetic image section also feature a flip-over photocathode 7/8" in diameter. The electrostatic sections, however, have a standard 2" diameter photocathode. The magnetic image section has a set of 17 kovar flanges, separated by 16 ceramic wafers. A linearly increasing potential is applied across the set of kovar flanges. With such an arrangement, field emission is less of a problem, since high electric field gradients are avoided.

b. Tube E-I

Tube E-I gave an unsatisfactory picture. It is believed that excessive cesium deposits on the target caused high lateral target leakage. The tube was
<table>
<thead>
<tr>
<th>Tube No.</th>
<th>Type of Scan</th>
<th>Image Section</th>
<th>Target Material</th>
<th>Target Diameter</th>
<th>Test Results</th>
</tr>
</thead>
<tbody>
<tr>
<td>E-I</td>
<td>Vidicon</td>
<td>Electrostatic</td>
<td>As$_2$S$_3$</td>
<td>7/16”</td>
<td>Poor. Excessive target fatigue.</td>
</tr>
<tr>
<td>E-II</td>
<td>Vidicon</td>
<td>Magnetic; flip-over photocathode</td>
<td>As$_2$S$_3$</td>
<td>7/16”</td>
<td>Good. Results given herein.</td>
</tr>
<tr>
<td>E-III</td>
<td>Vidicon</td>
<td>Magnetic; flip-over photocathode</td>
<td>As$_2$S$_3$</td>
<td>7/16”</td>
<td>Good. Results given herein.</td>
</tr>
<tr>
<td>E-IV</td>
<td>Vidicon</td>
<td>Electrostatic</td>
<td>As$_2$S$_2$</td>
<td>7/16”</td>
<td>Initially good. Results given herein.</td>
</tr>
</tbody>
</table>
incapable of storing a picture in the conventional manner, and it could not integrate a picture at low light levels. Furthermore, the target had a pronounced fatigue effect, in which the target sensitivity decreased as EBIC bombardment proceeded. In addition, the connections to the photocathode and to the target were imperfect; the result was an image which fluctuated continuously with time. Resolution was low, apparently as a result of the cesium deposition. For these reasons, no quantitative data were taken on this tube.

c. Tube E-II

Tube E-II made use of a magnetically focused image section, a 7/16" diameter target and vidicon scan. Its imaging performance was quite good. The tube was operated at magnetic field strengths near 100 gauss, and at image section voltages near 20 KV, giving picture quality similar to that obtainable on an ordinary camera pick-up tube. Fig. 23 gives a set of two photographs. Fig. 23a is taken at an input illumination of 8.7 x 10^{-4} ft-candles, with the target overscanned. The resolution is about 600 TV lines per inch. The lower photograph represents the target underscanned at maximum resolution. The light level is about 10^{-2} ft-candles, and the resolution visible on the original photograph is 1100 TV lines/inch. On the monitor, the limiting resolution in one direction only is about 1300 TV lines/inch at the center of the tube. The resolution characteristic, showing the number of TV lines per inch as a function of input illumination, is given in Fig. 24. In obtaining these data, the tube was operated at 17 KV, with 50 volts on the target. At manufacturing date, the photocathode sensitivity was 29 microamperes per lumen. Fifteen weeks later, the photocathode sensitivity had dropped to 15 microamperes per lumen. The data taken in Fig. 24 were obtained approximately ten weeks after the tube was manufactured. As shown in that figure, the best threshold was 3.5 x 10^{-3} ft-candles. The tube was operable at 20 KV, but there appeared to be little added value in operating at this potential.

For the conditions represented in Fig. 23, 7 to 8 shades of gray were visible. The persistence was only fair however, since even at high light levels, it took several seconds for the image to disappear. When the target voltage was raised to 50 volts after operation at a lower voltage, some of the previous information would show up on the target for a short time. This was true for images which were allowed to remain on the target for long periods of time.

During operation of the tube at 20 KV, the tube experienced a high-voltage breakdown, which was observable on the monitor and which persisted for an hour thereafter, even when the tube was operated as low as 15 KV. The socket surrounding the Kovar flanges prevented any visible determination of the exact location of the breakdown. Subsequently this effect disappeared.

After several days operation, the target was considerably slower in response than it had been initially. In fact, at a light level of 8 x 10^{-4} ft-candles, it was about 600 seconds before the gain had risen to 100, gain being here defined as the ratio of the target signal current to the photocathode current.
Fig. 23-a - Resolution 600 TV lines/inch at an input illumination of $8.7 \times 10^{-4}$ ft-candles. Target is overscanned in this photograph.

Fig. 23-b - Resolution on photograph was 1100 TV lines/inch at a light level of the order $10^{-2}$ ft-candles. Target is underscanned.

Fig. 23 - Photographs of Display from E-II Ebicon.
Fig 24 - Resolution vs input illumination for magnetically focused electron beams.

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In response to a given photocathode current, the target current slowly would rise, at the same time as the image became increasingly visible.

When operated prior to insertion into the tube, the target had a gain of $450$ at $20\,\text{KV}$ and $50\,\text{volts}$ on the target. As first measured in the tube at $50\,\text{volts}$ target and at $16\,\text{KV}$ on the image section, the gain was $187$, for an input current corresponding to an illumination of $5.5 \times 10^{-5}\,\text{ft-candles}$. This value was obtained early in the life of the tube when the persistence was a few seconds, but as was pointed out, the target became slower after several days operation.

The target was relatively free from blemishes, had good contrast and normal storage characteristics. Except for the persistence, it was satisfactory in every visual characteristic. It is interesting to note that $\text{As}_2\text{S}_2$ targets, see E-IV, appear to be less susceptible to long term persistence effects.

Satisfactory focus could be achieved in a number of different modes. The tube was operated with a linear gradient from the photocathode to the last Kovar flange before the target. The voltage on this last Kovar could be adjusted over a wide range, keeping the photocathode-to-target voltage constant. Corresponding to this voltage on the last flange, a value of magnetic field could generally be found which would focus the image section. Since the scan and image sections were focused by the same magnetic coil, it was necessary to readjust the voltage on grid 3 of the scan section to achieve focus for the new magnetic field. Perhaps the best focus was obtained with $4.6\,\text{KV}$ between photocathode and the last Kovar flange when the photocathode-to-target voltage was $16\,\text{KV}$, but the advantage of this mode over other modes was slight. For these various modes, the required focus current varied from $80-150\,\text{gauss}$.

The resolution of the tube in TV lines/inch was of the order of $1100$. Under optimum conditions it was about $1300\,\text{TV lines/inch}$ in one direction. For a $7/16\,\text{"}$ diameter target, useful over $80\%$ of its diameter, this yields about $450\,\text{TV lines}$.

The minification from photocathode to target was about $1.5$. This gave a useful photocathode diameter of about $0.67\,\text{ inches}$. It is evident that a larger area photocathode would result in proportionally low thresholds.

The general construction of the tube is shown in Fig. 25.

d. Tube E-III

The performance of tube E-III was similar to that of tube E-II. Resolution data are shown as a series of points on Fig. 25; these data show that the maximum resolution was somewhat higher than that of E-II, but that the tube was perhaps less sensitive at the low line numbers. This latter effect might be attributed to the $18\,\text{microampere per lumen photosurface}$ which
Fig. 25—Magnetically focused EBIC camera tube with vidicon scan
E-III had when constructed. Fourteen weeks later the response had dropped to 6.7 microamperes per lumen. Actual testing was done about nine weeks after manufacture.

This tube was similar to E-II also in that initially the target had a few seconds delay before either full gain or full erasure was realized. At a later testing however, the target was slower; for example, at a light level of $2.7 \times 10^{-4}$ ft-candles, 35 seconds delay were required to realize a target gain of 100. At one of the threshold measurements, 100 seconds of viewing were necessary before the image became visible.

Although the tube was operable at least to 20 KV, there seemed to be little advantage in raising the photocathode-to-target voltage above 17 KV.

General imaging quality was good, being very similar to tube E-II. The general comments on imaging and focusing, described under E-II, also apply to this tube. As many as 9 shades of gray were seen. Resolution was the same in either of two perpendicular directions, and was reasonably uniform over the whole tube.

One section of the photocathode, about 20% of the entire area, had higher photosensitivity; this was noticeable particularly in photographs of the monitor, but not particularly objectionable in direct viewing. On the opposite edge of the target, there was an area which appeared bright when the high voltage was turned on. The target would then charge in a matter of a few seconds, and would operate normally. This charging effect was more noticeable than that which appears on the normal tube.

e. Tube E-IV

This tube, which made use of electrostatic focus on the image section and vidicon scan, was similar in structure to tube E-I except that the support structure of the target was divorced electrically from the last electrode of the image section lens system. This change in design permitted grounding the last electrode, thus allowing it to serve as a guard ring. This helped to minimize interference in the target signal circuit produced by high voltage instabilities in the image section. The revised structure also had the advantage of lowering the capacity of the target electrode.

The photoresponse as the tube came off exhaust was of the order of 30 ua/lumen. The initial performance of the tube was excellent. The tube operated stably to 14 KV, but little increase in threshold was noted as the target was increased from 10 KV to 14 KV.

The indications were that tube resolution was in excess of 400 TV lines. From rough tests the imaging threshold was estimated to be of the order of $10^{-6}$ ft-candles. The speed of response of the As$_2$S$_3$ target was excellent. Even after a 4 minute exposure at relatively high light level, very little trace of after image was noted.
Upon resuming testing after a 4 day interval, the initiation of gas discharges in the image section for voltages in excess of 500 volts was noted. The presence of gas in the tube was confirmed by a rise in photoresponse to 48 ua/lumen. The tube getter was flashed and all glass-to-metal seals painted with glyptol. Photoresponse dropped to 10 ua/lumen and rose within a day to about 20 ua/lumen.

Unfortunately the high voltage stability of the tube was affected by the sequence of events. Two cold-emission bright spots could be observed on the monitor image of the target when the image section had 7 KV impressed across it. As voltage was raised, the general field emission background increased rapidly. At 10 KV high voltage flashing commenced.

The tube was rechecked after a 6 week interval. Photoresponse was still of the order of 20 ua/lumen, and the high voltage characteristics of the tube were observed to remain substantially unchanged. The threshold for imaging was determined to occur when 2.0 x 10^{-5} ft-candles were impressed on the photocathode for 10 KV on the image section and 36 target volts. This corresponds to an input current of about 8 x 10^{-12} amperes, and a signal current at target of about 7.5 x 10^{-10} amperes. On the demountable position thresholds below 10^{-13} amperes are frequently observed. Target gain was of the order of 100 for input currents between 8 x 10^{-12} and 2 x 10^{-10} amperes. However, the ability to observe threshold signals was very much affected by field emission. The speed of response of the target to both low and high signal levels remained excellent.

This target, which consisted of a 0.25 micron layer of Sb_{2}S_{3} on a 1.4 micron layer of As_{2}S_{3} evaporated over an aluminized self-supporting Al_{2}O_{3} layer, originally had a target gain of about 600 at 50 target volts and 20 KV.

6) Conclusions

While the tubes constructed to date with vidicon scan have not reached the sensitivity theoretically, Ref. 16, attainable, they appear to be within a factor of 10 of the achievable value. The difference between tube performance and theory appears to be related to the signal-to-noise ratios at which the tubes will operate. Tests in the demountable vidicon scan position have indicated that the imaging threshold of present EBIC targets corresponds to target signal currents of the order of 2 x 10^{-10} amperes. According to these results, the targets will threshold at a signal-to-noise ratio of 0.1, as compared to signal-to-noise ratios somewhat less than .01 as determined in the background work involved in the derivations of Ref. 16. Further work is required to investigate the discrepancies involved.

It is believed that a better understanding of the factors involved in determining the electron absorptivity of scanned targets may prove fundamental to the developing of better targets of the EBIC and PC type.
Because of the problems involved in making reliable measurements in a demountable position, it is recommended that the test work on improving targets be conducted under more rigorous vacuum environments. In fact, it is necessary to also investigate the effect of subjecting the targets to atmospheric conditions, as is now the case. The properties of many targets are radically affected by exposure to the atmosphere, including the humidity conditions which prevail. Work on such targets cannot be performed without arranging to fabricate and test the targets in the same vacuum position in which they are fabricated.

Such a program would make it possible to fabricate the targets, test them, and then subject them to various controlled conditions, such as elevated temperatures, exposure to cesium, etc. Should targets be developed which are damaged by atmospheric exposure, the injection technique affords a convenient method for inserting them in tubes after fabrication, testing them, and selecting a suitable target.
LIST OF REFERENCES


<table>
<thead>
<tr>
<th>Cyg</th>
<th>ACTIVITIES AT WPAFB</th>
<th>Cyg</th>
<th>Air Force (Cont'd)</th>
</tr>
</thead>
<tbody>
<tr>
<td>1</td>
<td>ASAFR (UTS Review)</td>
<td>1</td>
<td>Commander</td>
</tr>
<tr>
<td>1</td>
<td>ASAFR (Library)</td>
<td></td>
<td>Electronic Systems Division</td>
</tr>
<tr>
<td>3</td>
<td>ASAFP</td>
<td></td>
<td>L. G. Hanscom Field</td>
</tr>
<tr>
<td>2</td>
<td>ASAFRS-1</td>
<td></td>
<td>Bedford, Massachusetts</td>
</tr>
<tr>
<td>10</td>
<td>ASAFRT-2</td>
<td>1</td>
<td>Commander</td>
</tr>
<tr>
<td>10</td>
<td>ARX</td>
<td></td>
<td>Space Systems Division</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>Air Force Post Office</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>Los Angeles, California</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>Navy</td>
</tr>
<tr>
<td></td>
<td></td>
<td>1</td>
<td>Chief</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>Bureau of Ships</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>ATTN: Mrs. F. R. Darne, Code 69LA</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>Washington 25, D.C.</td>
</tr>
<tr>
<td>1</td>
<td>Commander</td>
<td>1</td>
<td>Naval Research Laboratory</td>
</tr>
<tr>
<td></td>
<td>Air Force Special Weapons Center</td>
<td></td>
<td>ATTN: Mr. J. Rogge</td>
</tr>
<tr>
<td></td>
<td>ATTN: SWOI</td>
<td></td>
<td>1207 Nicholsen Laboratory</td>
</tr>
<tr>
<td></td>
<td>Kirtland Air Force Base, New Mexico</td>
<td></td>
<td>China Lake, California</td>
</tr>
<tr>
<td>1</td>
<td>Commander</td>
<td>1</td>
<td>Army</td>
</tr>
<tr>
<td></td>
<td>Air Force Missile Test Center</td>
<td></td>
<td>Commanding General</td>
</tr>
<tr>
<td></td>
<td>ATTN: AMIC Tech, Library MU-135</td>
<td></td>
<td>U. S. Army Engineer Research and Development Laboratory</td>
</tr>
<tr>
<td></td>
<td>Patrick AFB Fla</td>
<td></td>
<td>ATTN: Warfare Vision Branch</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>Ft. Belvoir, Virginia</td>
</tr>
<tr>
<td>1</td>
<td>Commander</td>
<td>1</td>
<td>Commanding Officer</td>
</tr>
<tr>
<td></td>
<td>Air Proving Ground Center</td>
<td></td>
<td>U. S. Army Signal Research and Development Laboratory</td>
</tr>
<tr>
<td></td>
<td>ATTN: FORTI</td>
<td></td>
<td>ATTN: SIGFR/LG-FRC</td>
</tr>
<tr>
<td></td>
<td>Eglin Air Force Base, Florida</td>
<td></td>
<td>Ft. Monmouth, New Jersey</td>
</tr>
<tr>
<td>1</td>
<td>Commander</td>
<td>1</td>
<td>Commanding Officer</td>
</tr>
<tr>
<td></td>
<td>Ballistic Systems Division</td>
<td></td>
<td>U. S. Army Electronic Proving Ground</td>
</tr>
<tr>
<td></td>
<td>Air Force Post Office</td>
<td></td>
<td>ATTN: Combat Area Surveillance Department</td>
</tr>
<tr>
<td></td>
<td>ATTN: WATG</td>
<td></td>
<td>Ft. Huachuca, Arizona</td>
</tr>
<tr>
<td></td>
<td>Los Angeles, California</td>
<td></td>
<td>Army</td>
</tr>
<tr>
<td>1</td>
<td>Commander</td>
<td>1</td>
<td>Commanding General</td>
</tr>
<tr>
<td></td>
<td>Air Force Missile Development Center</td>
<td></td>
<td>Frankford Arsenal</td>
</tr>
<tr>
<td></td>
<td>ATTN: MDQRT-1</td>
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<td>ATTN: Dr. W. L. Chwelow, 1330</td>
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<tr>
<td></td>
<td>Holloman Air Force Base, New Mexico</td>
<td></td>
<td>Philadelphia 37, Pennsylvania</td>
</tr>
</tbody>
</table>

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<table>
<thead>
<tr>
<th>Cws</th>
<th>OTHER U.S. GOVERNMENT AGENCIES</th>
</tr>
</thead>
<tbody>
<tr>
<td>30</td>
<td>Armed Services Technical Information Agency</td>
</tr>
<tr>
<td></td>
<td>ATTN: TIPGR</td>
</tr>
<tr>
<td></td>
<td>Arlington Hall Station</td>
</tr>
<tr>
<td></td>
<td>Arlington 12, Virginia</td>
</tr>
<tr>
<td>100</td>
<td>Office of Technical Services</td>
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<td></td>
<td>Department of Commerce</td>
</tr>
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<td></td>
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<tr>
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<td>Advisory Group on Electronic Devices</td>
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<td>ATTN: Secretary, Working Group on Special Devices</td>
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<tr>
<td></td>
<td>346 Broadway, 6th floor</td>
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<td>New York 13, New York</td>
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**NON-GOVERNMENT INDIVIDUALS AND ORGANIZATIONS**

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|     | Santa Monica, California |
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|     | Lexington 73, Massachusetts |
Aeronautical Systems Division, Dir/Avionics, Electronic Technology Lab, Wright-Patterson AFB, Ohio. 
Rpt Nr ASD-TR-61-657. RESEARCH ON ELECTRON BOMBARDMENT INDUCED CONDUCTIVITY TARGETS IN CAMERA TUBES. Final report, Apr 62, 64p. incl illus., tables, 16 refs. 

Unclassified Report

An analysis of scan parameters as they affect the performance of electron bombardment induced conductivity (EBIC) targets is presented. The conclusion is reached that the secondary emission characteristic of the target surface is an extremely important parameter in camera tubes of the photo-

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1. Electron tubes
2. Camera tubes
3. Electron bombarding induced conductivity

I. AFSC Project 4156, Task 415605
II. Contract AF33(616)-6496
IV. J. Lempert and G. Klotzbaugh
V. In ASTIA collection
VI. Avail fr OTS

Aeronautical Systems Division, Dir/Avionics, Electronic Technology Lab, Wright-Patterson AFB, Ohio. 
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